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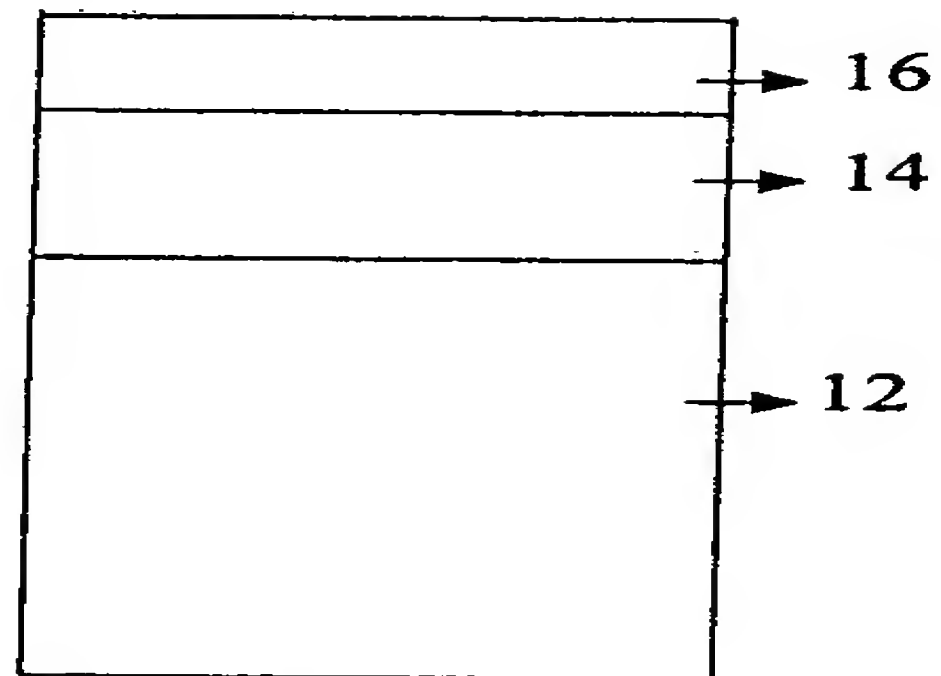


FIG. 1

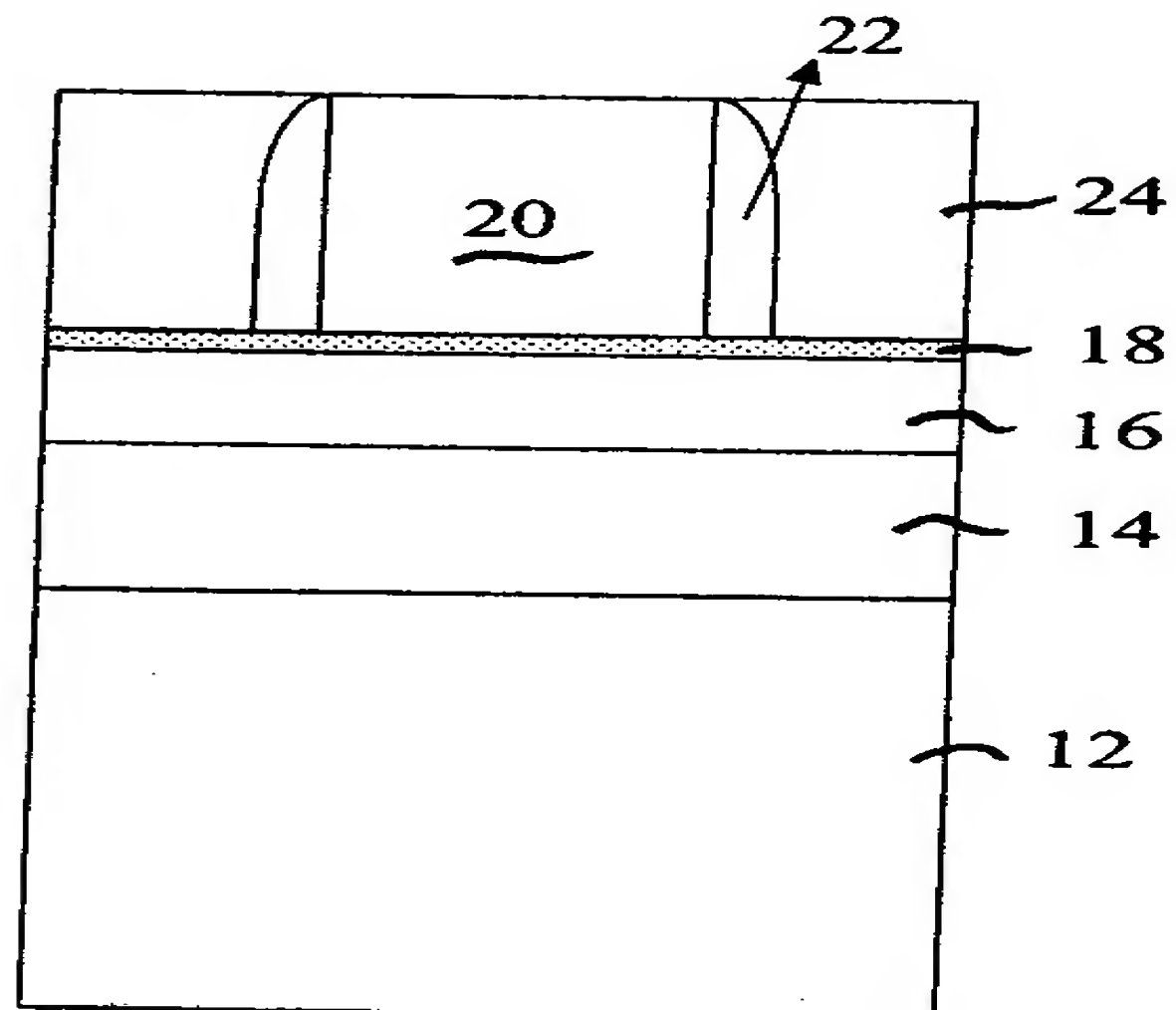


FIG. 2

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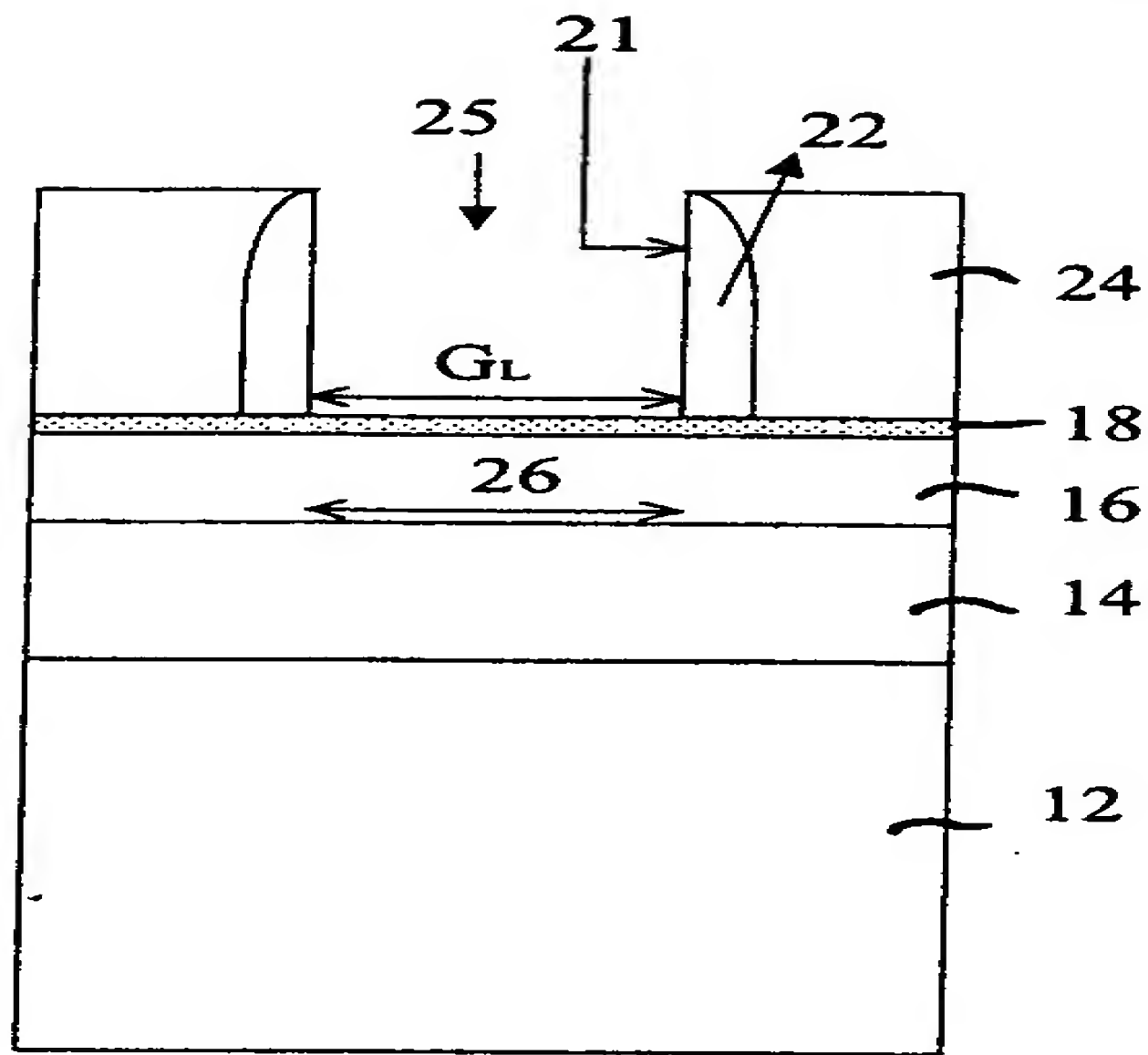


FIG. 3

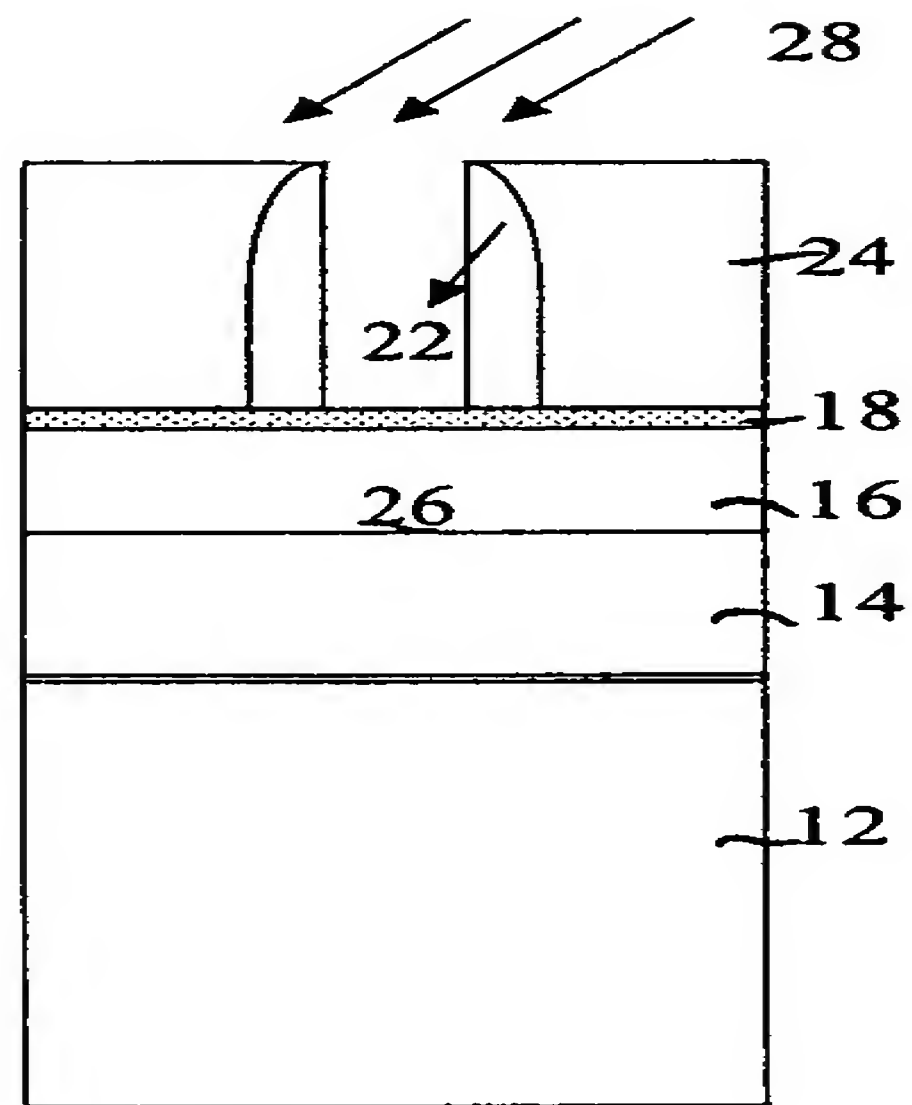


FIG. 4A

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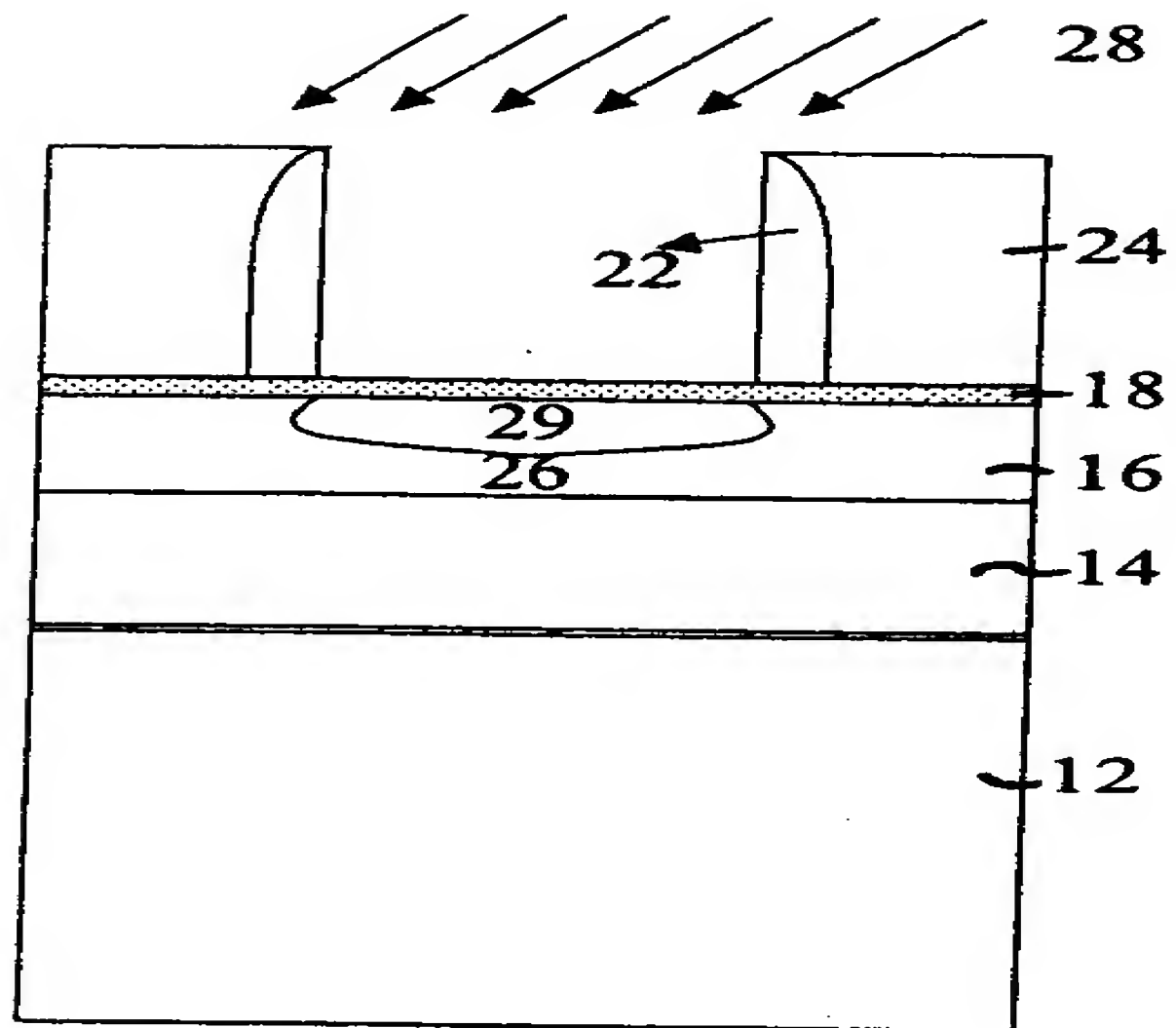


FIG. 4B

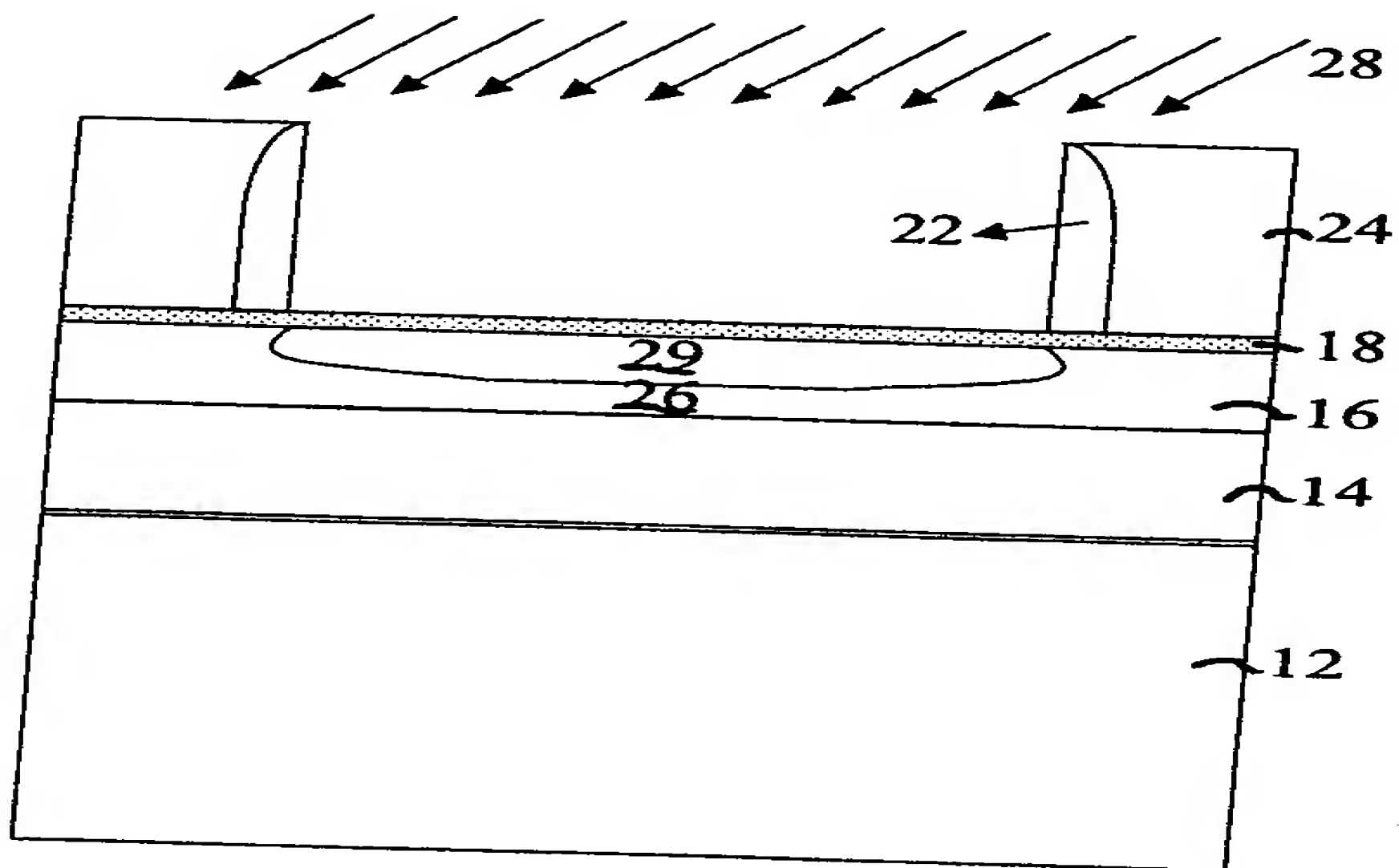


FIG. 4C

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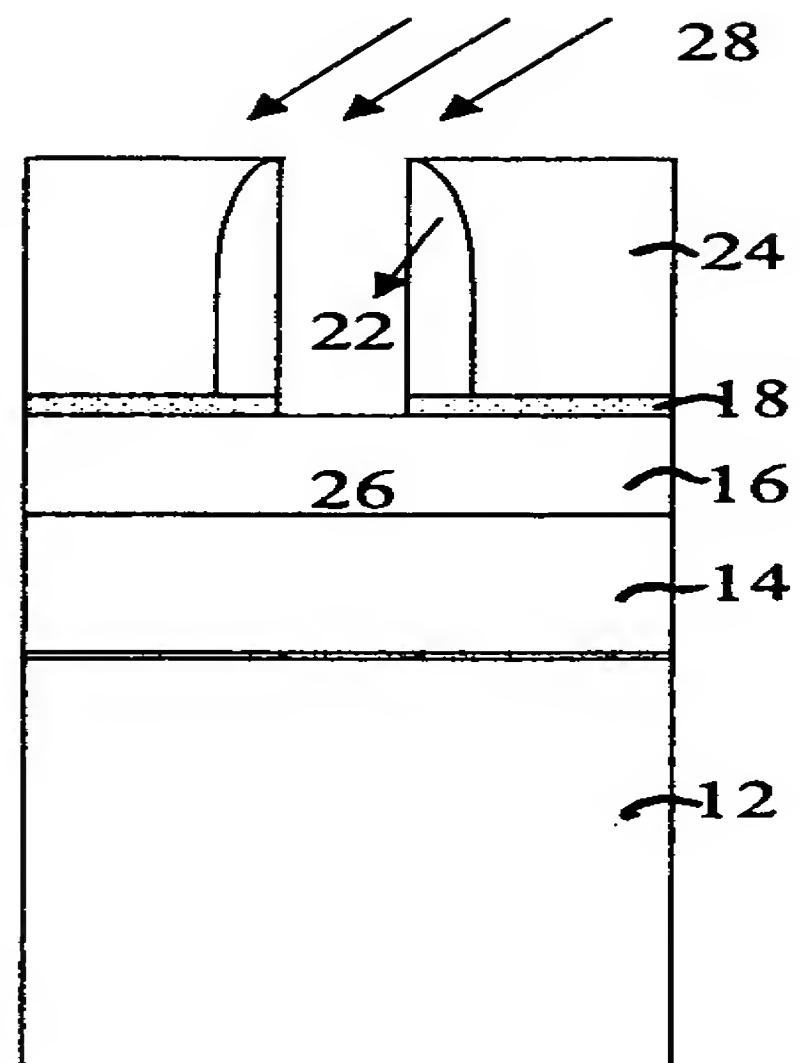


FIG. 5A

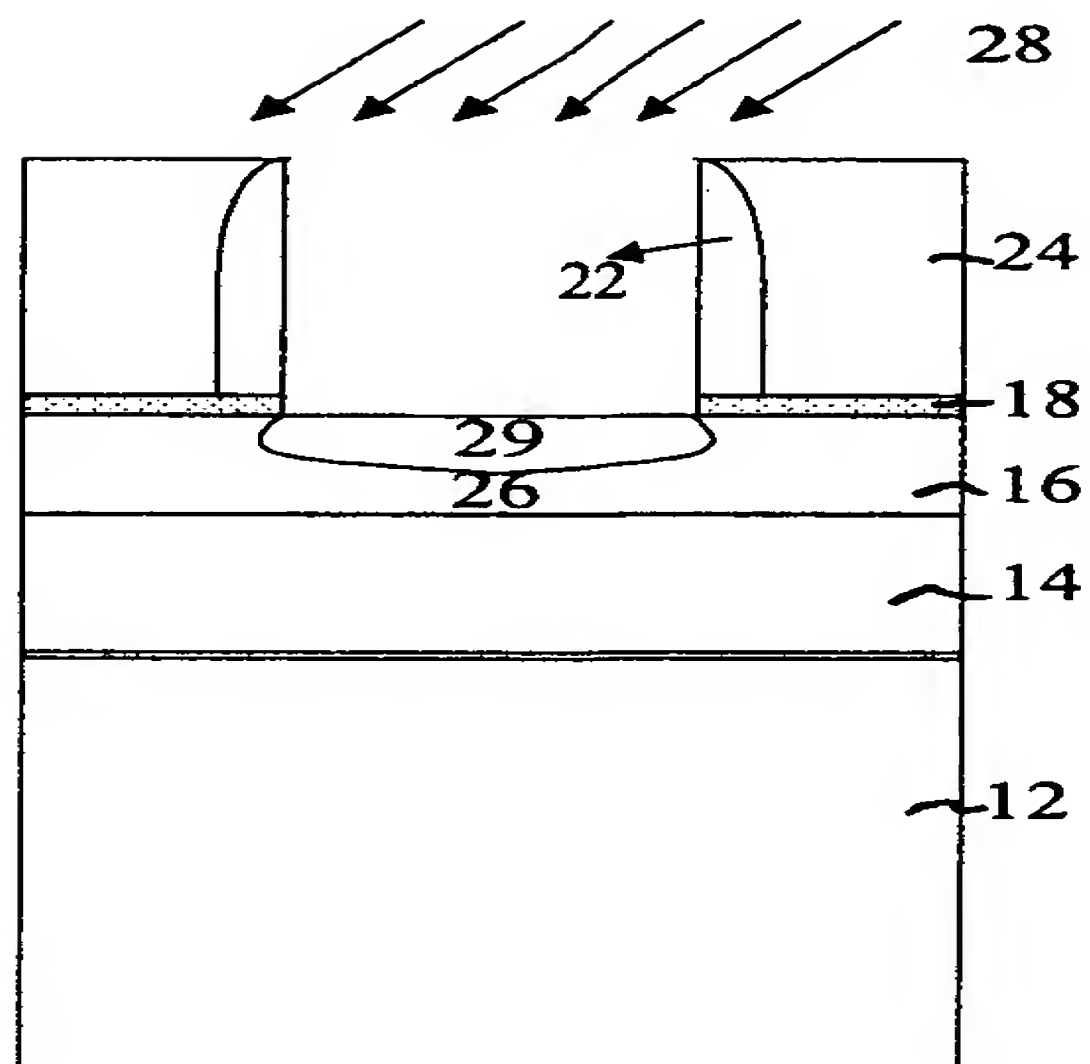


FIG. 5B

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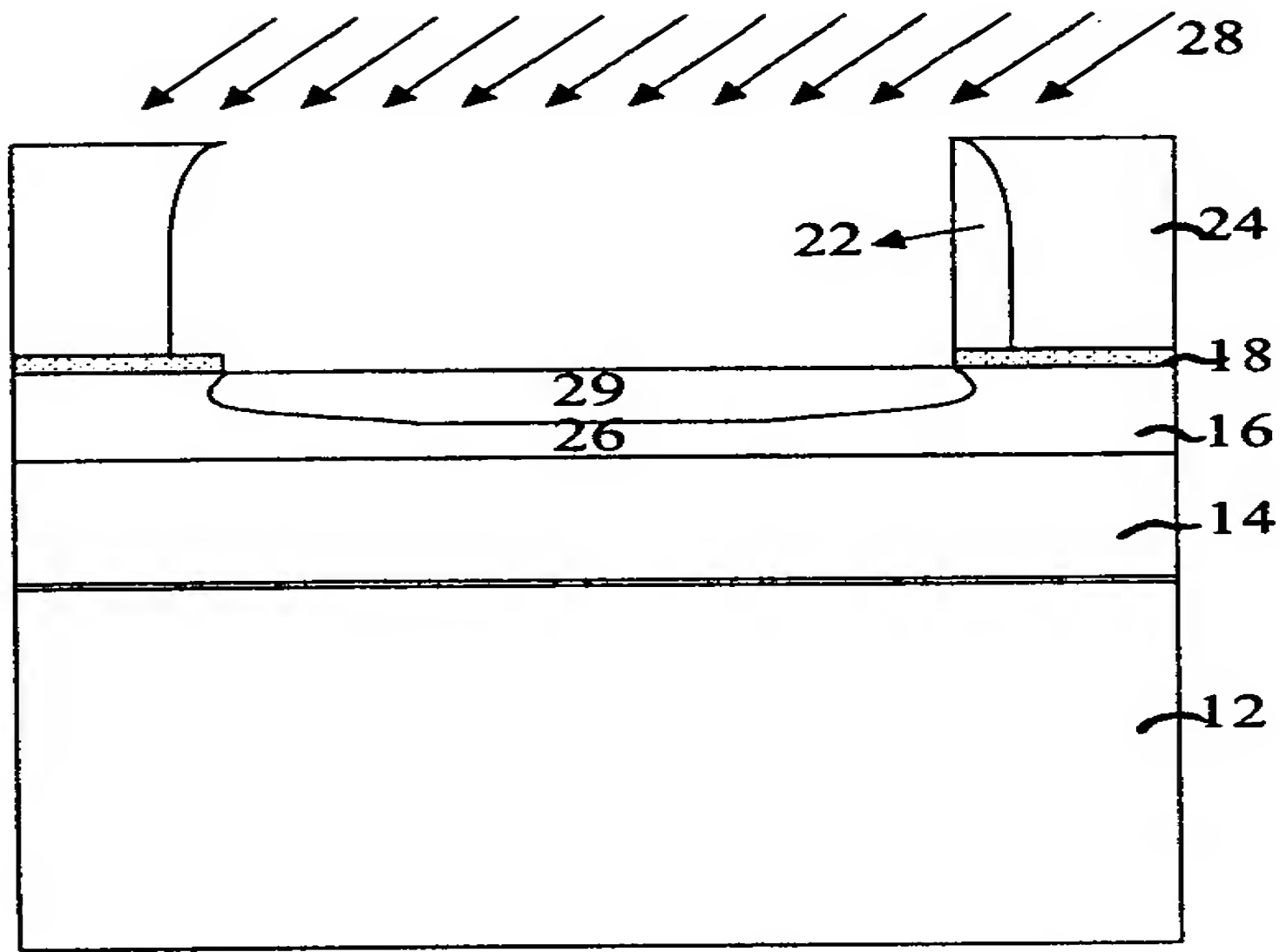


FIG. 5C

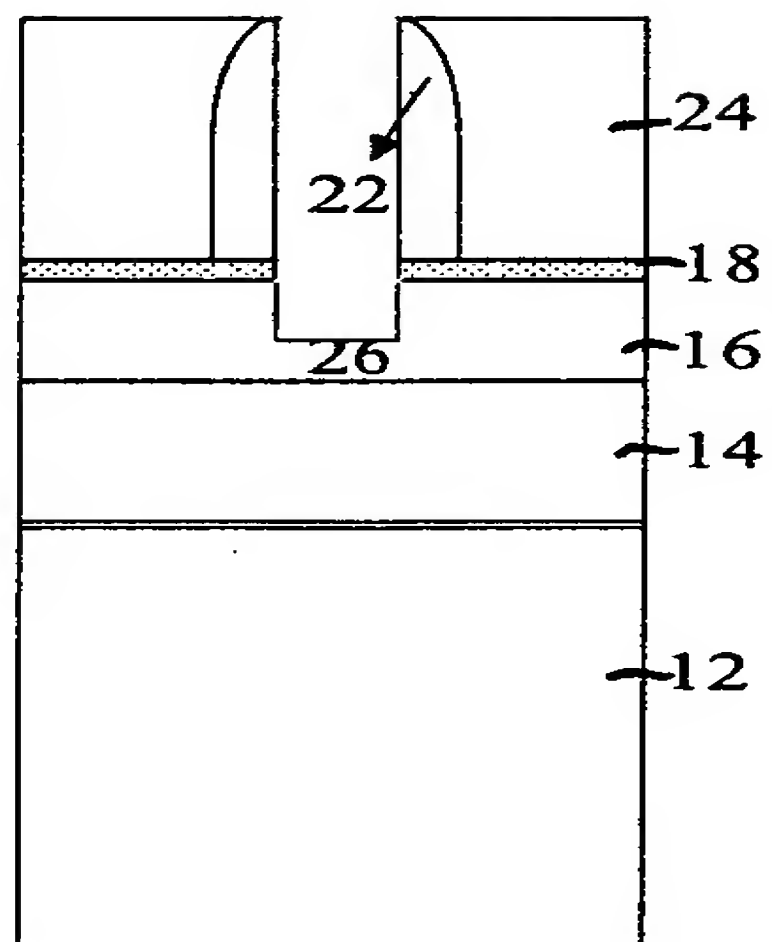


FIG. 6A

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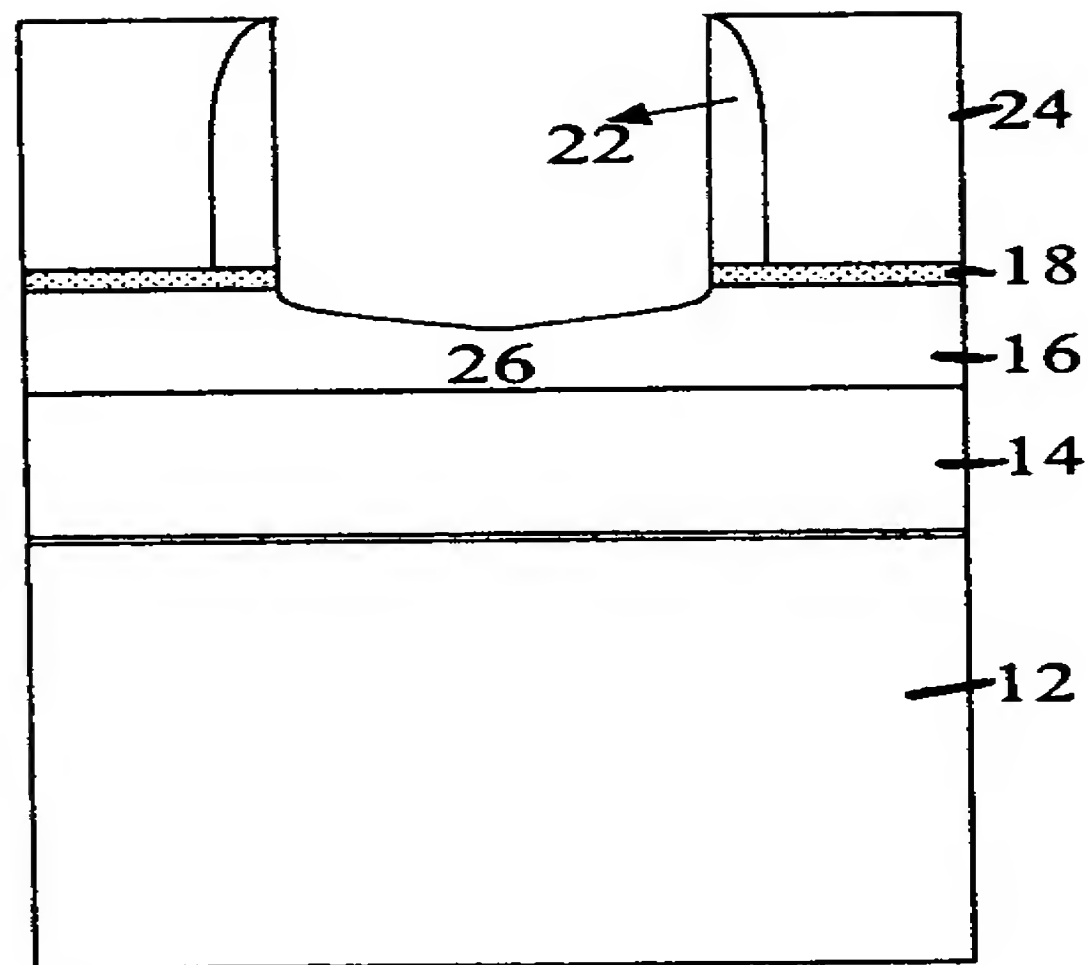


FIG. 6Bi

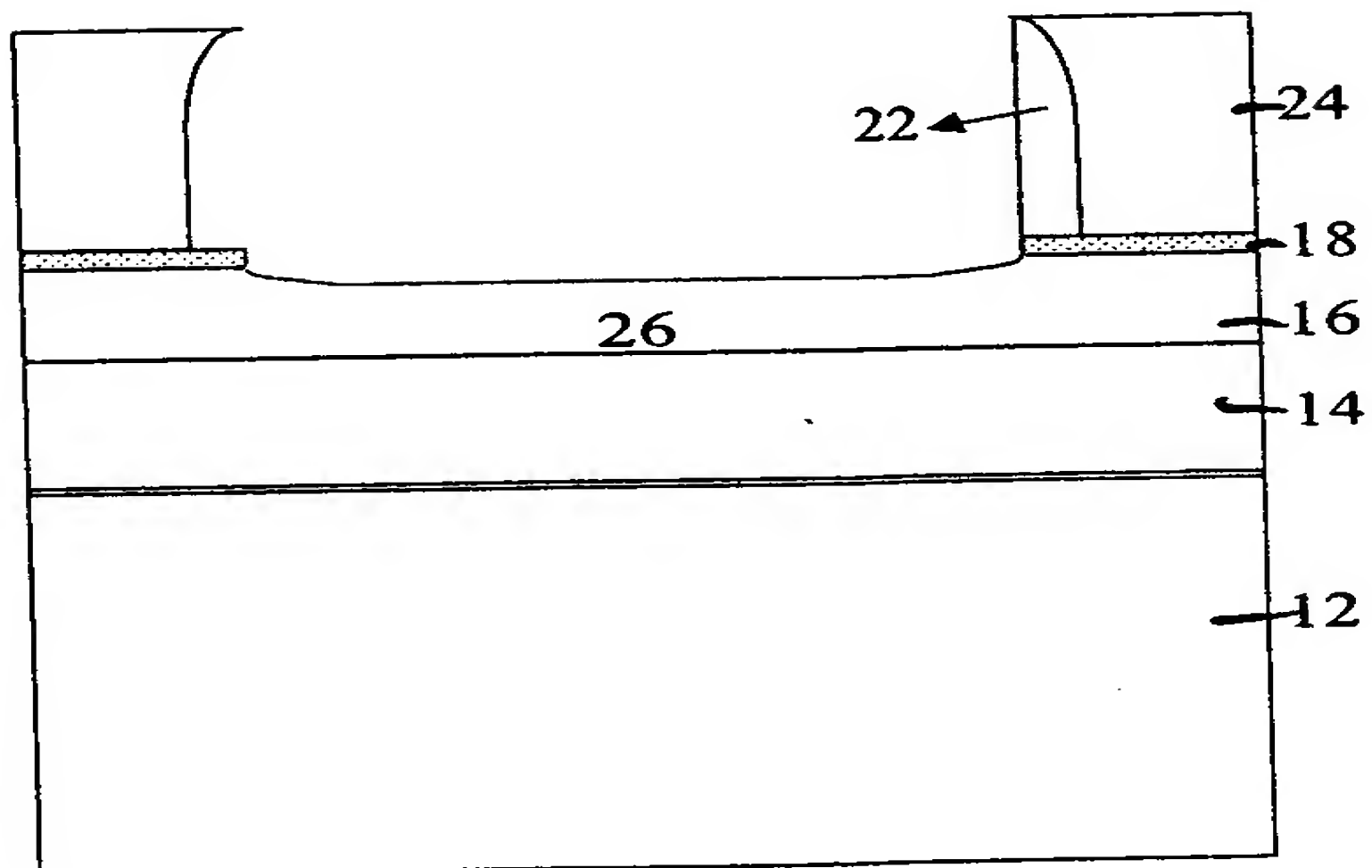


FIG. 6Ci

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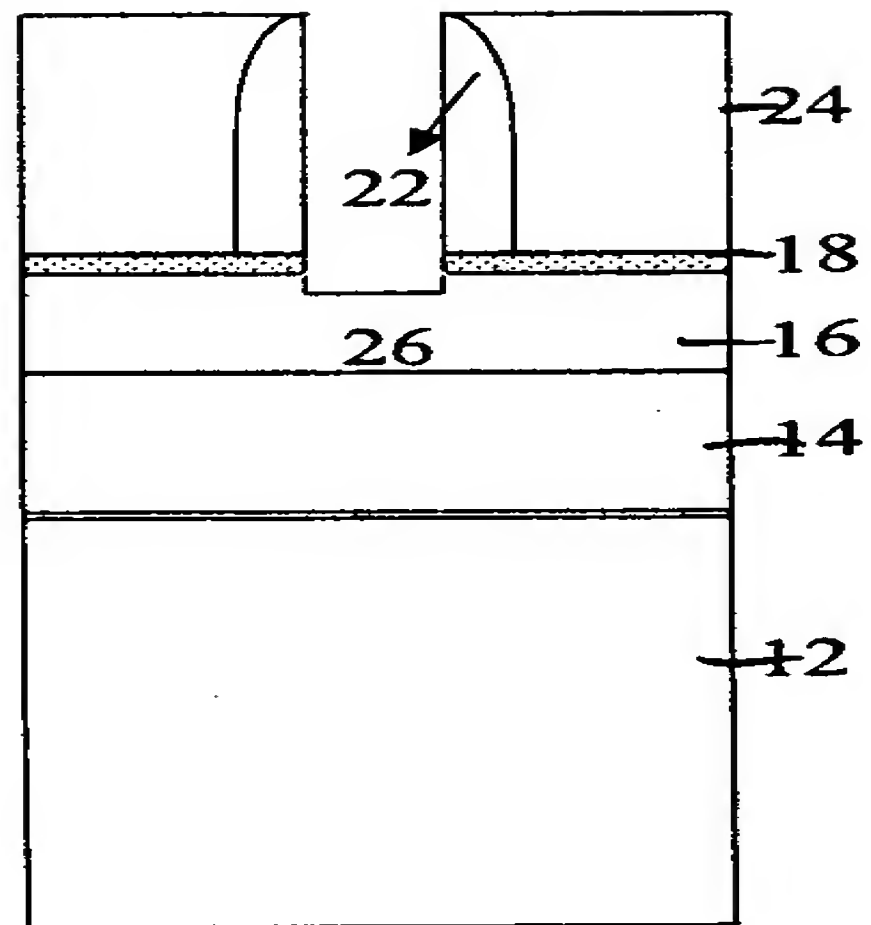


FIG. 6 A ii

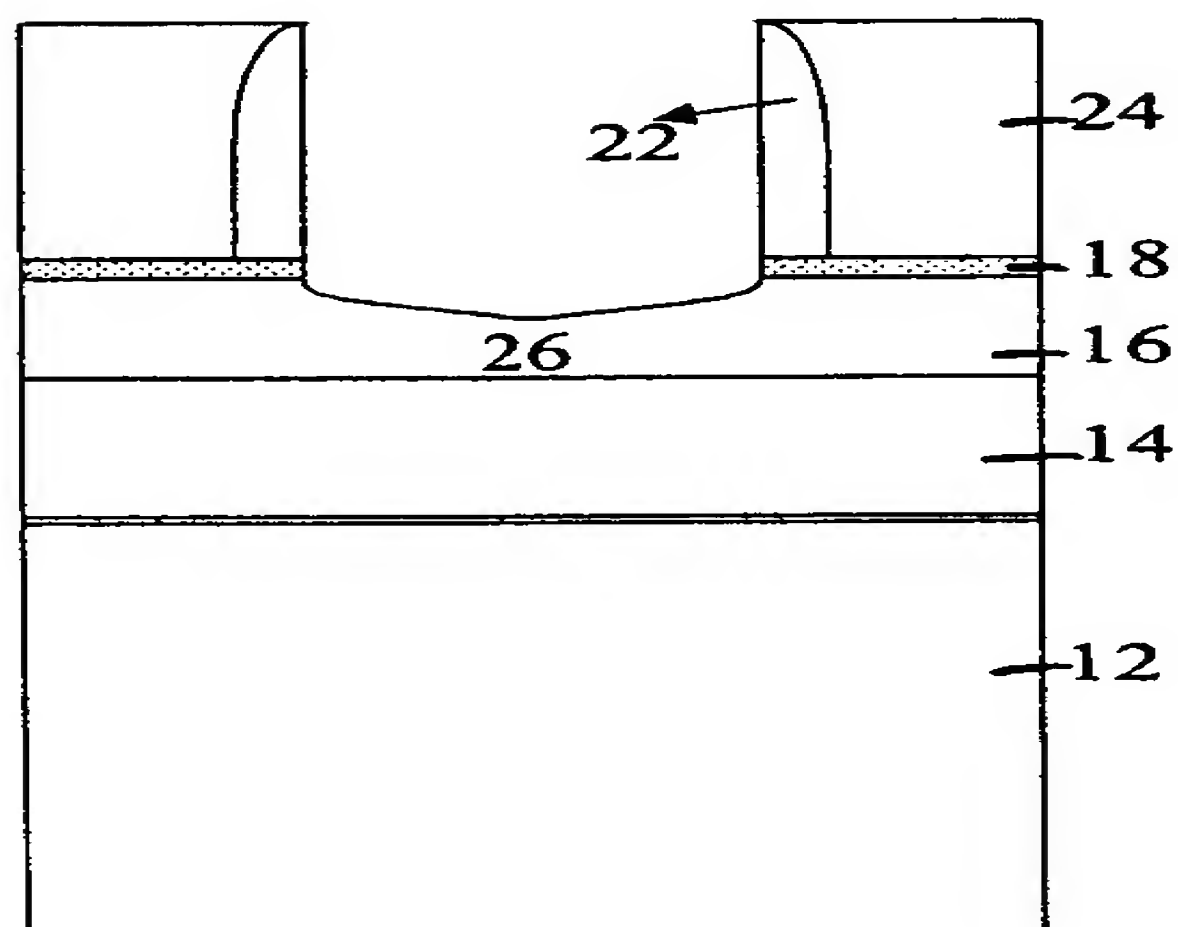


FIG. 6 B ii

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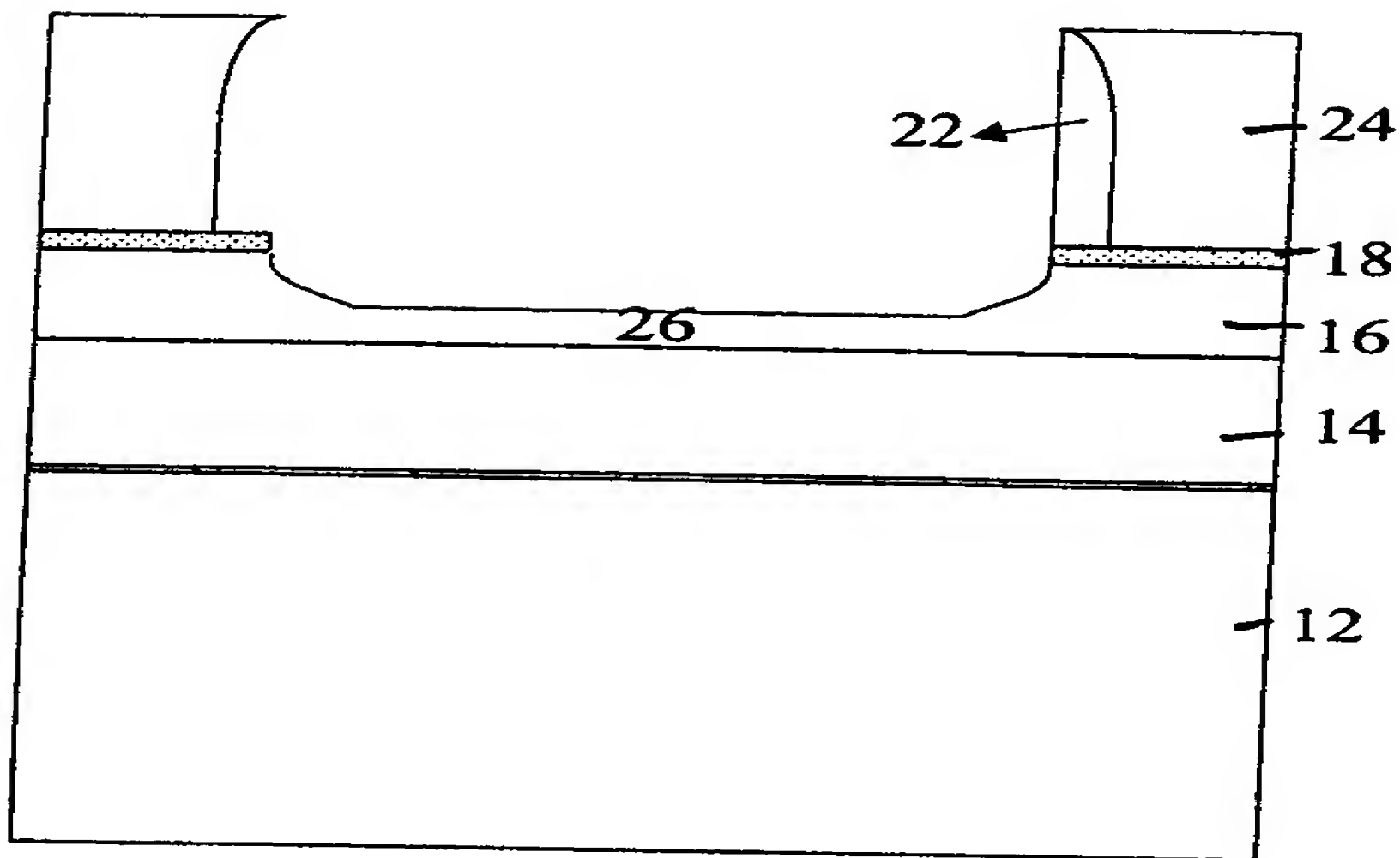


FIG. 6 Cii

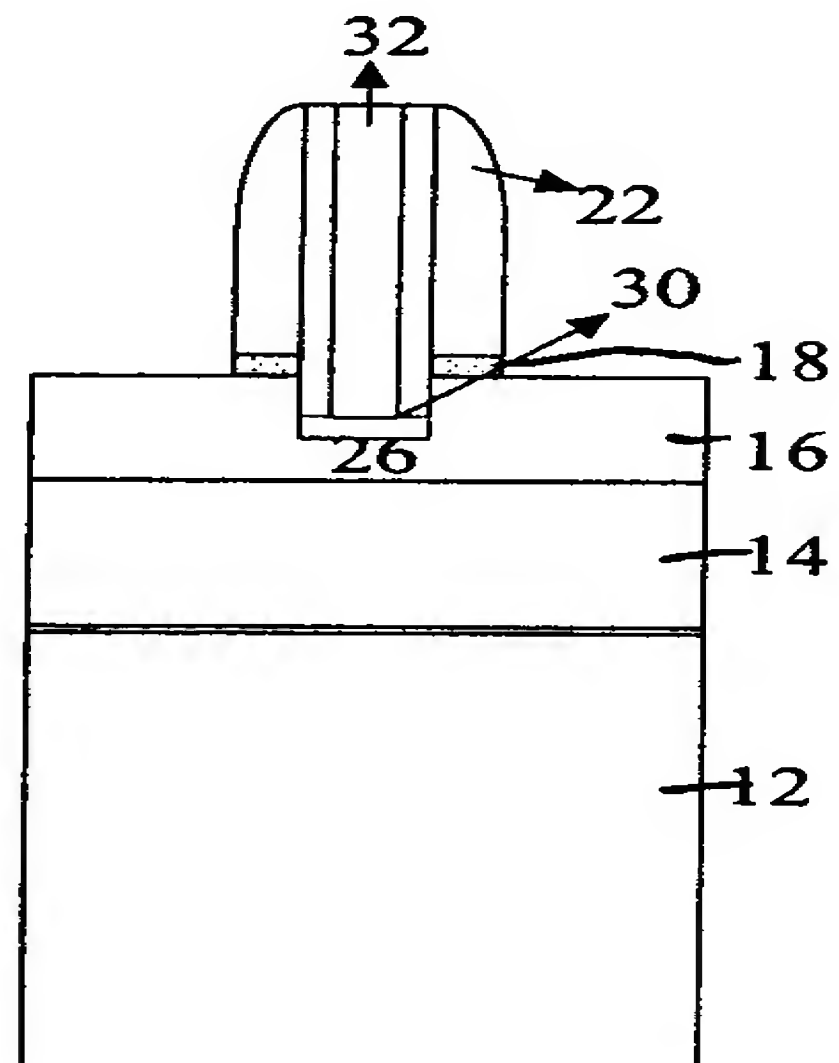


FIG. 7A

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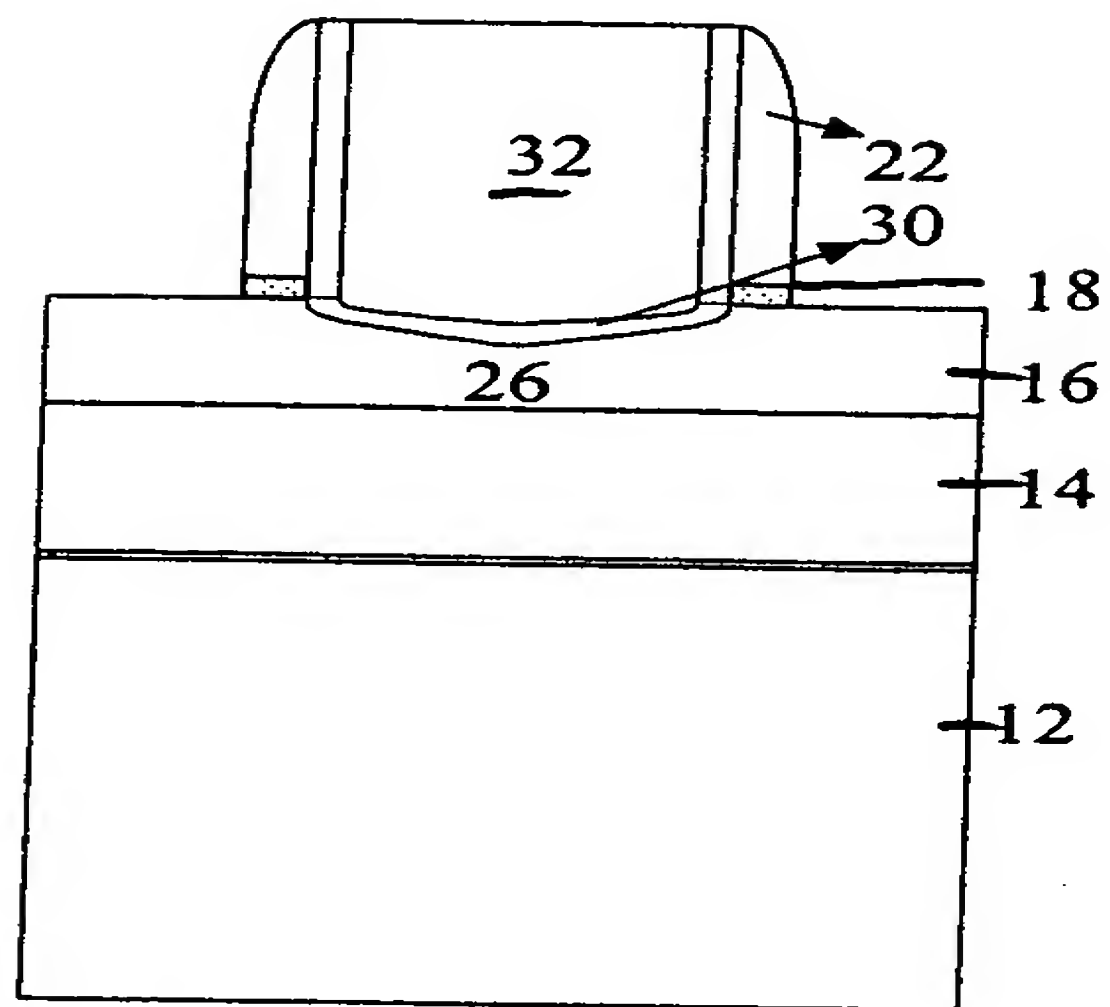


FIG. 7B

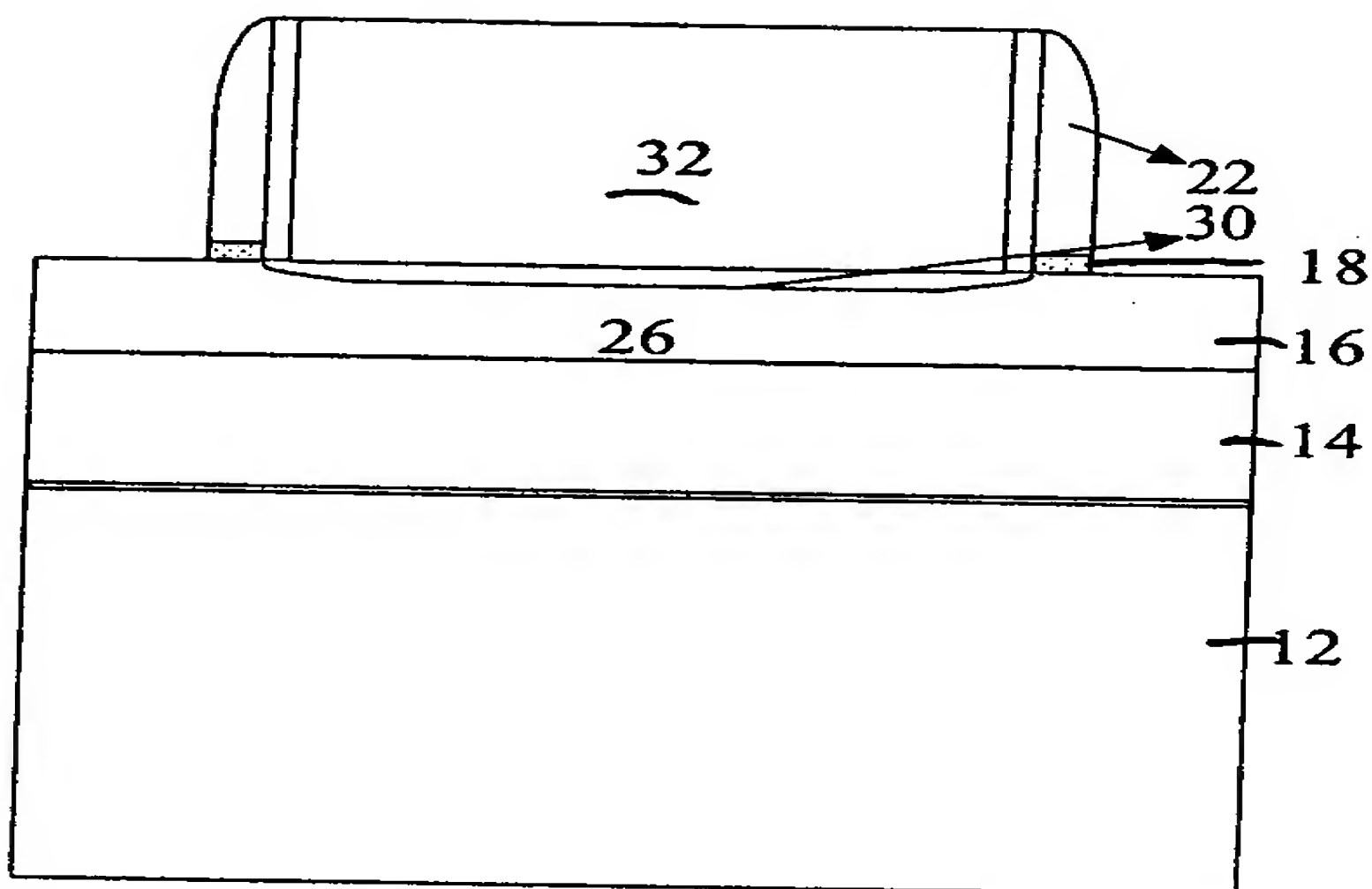


FIG. 7C

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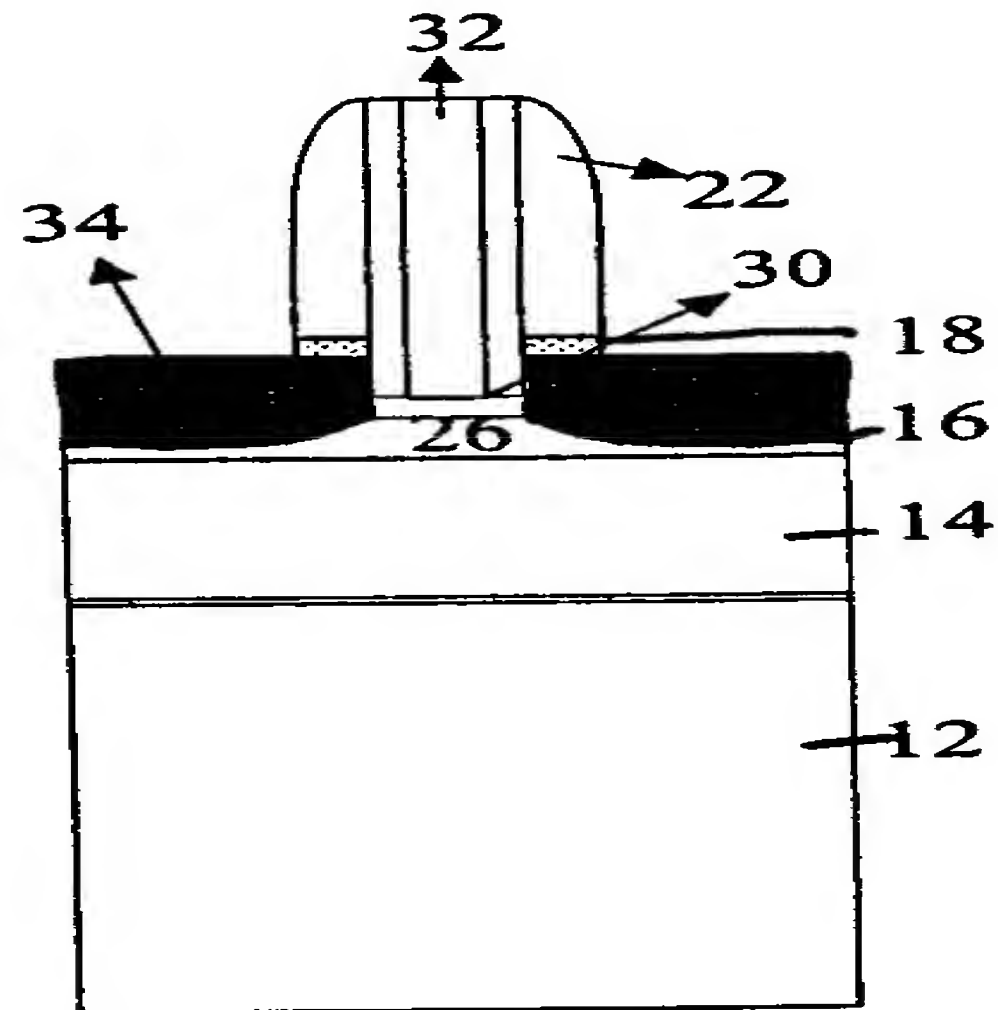


FIG 8A

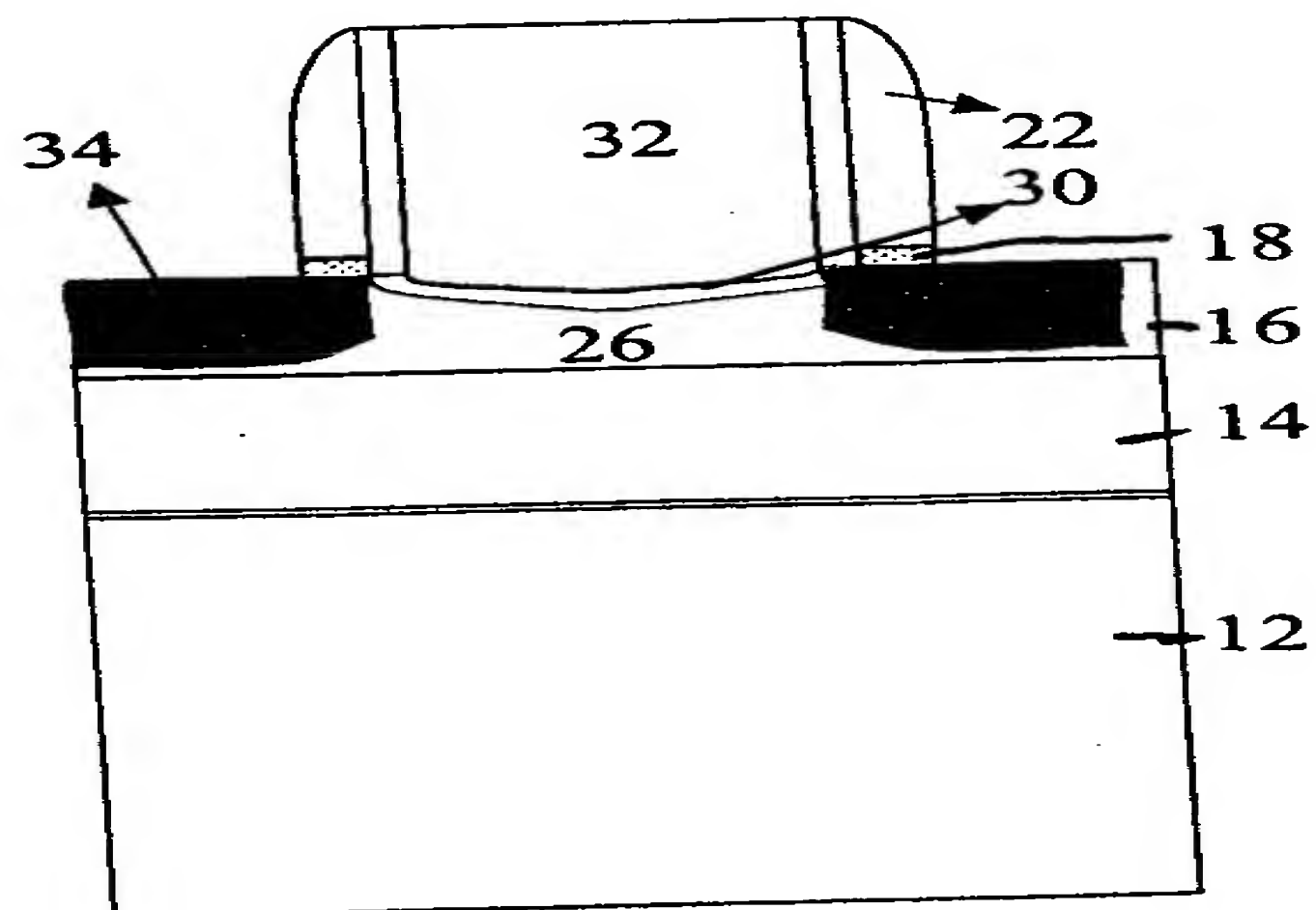
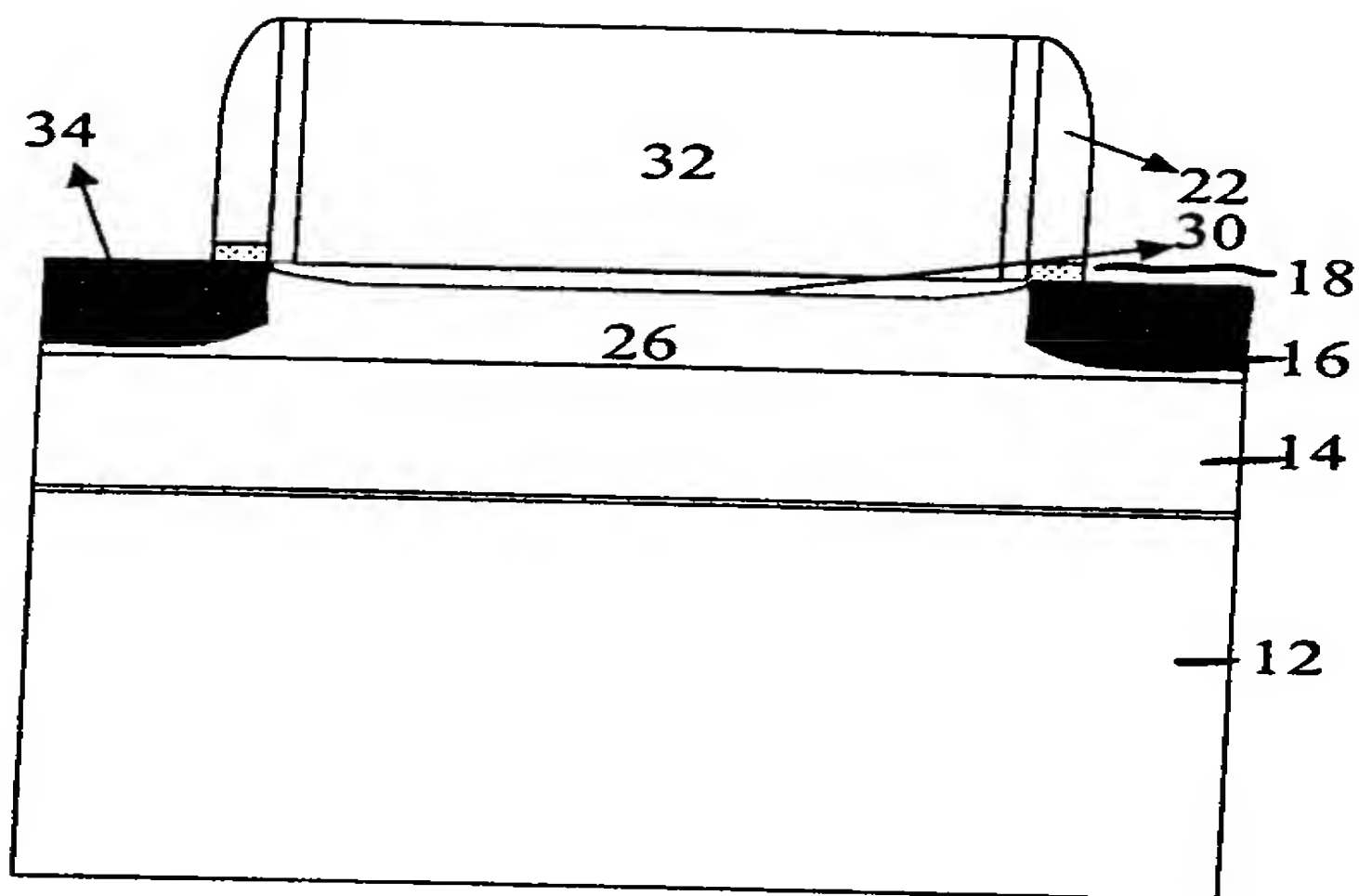


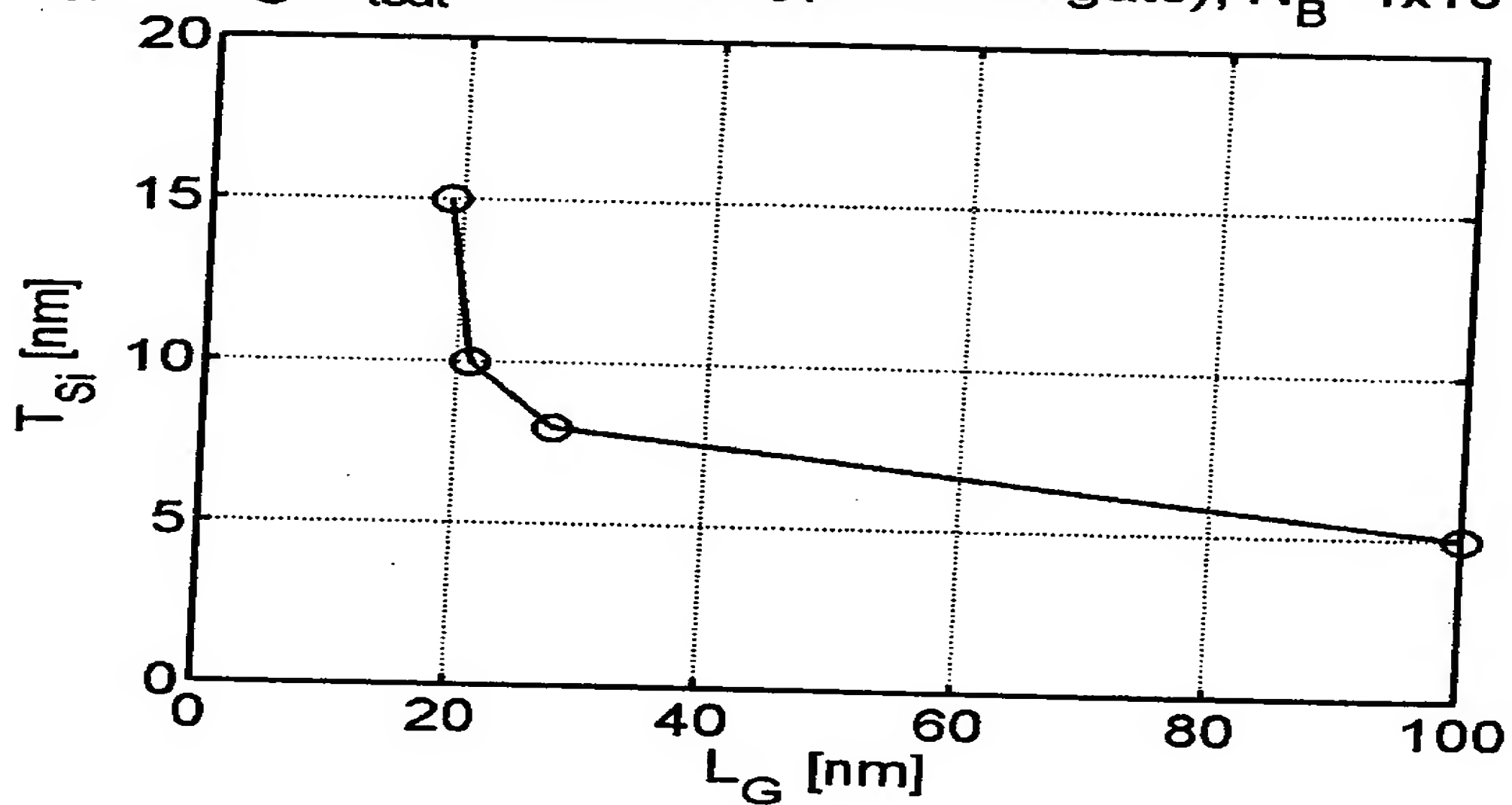
FIG 8B

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F16.8C

T_{Si} vs. L_G , $V_{tsat}=0.26V$ (n-type metal gate), $N_B=1 \times 10^{19} \text{cm}^{-3}$



F16.9